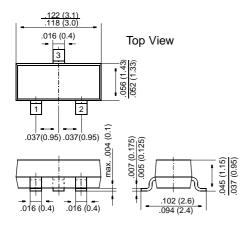
BAT54 THRU BAT54S

Schottky Diodes

<u>SOT-23</u>



Dimensions in inches and (millimeters)

Top View

These diodes feature very low turn-on voltage and fast switching.

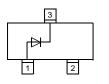
 These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.



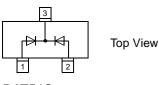
MECHANICAL DATA

FEATURES

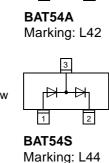
Case: SOT-23 Plastic Package Weight: approx. 0.008 g



BAT54 Marking: L4



12BAT54CMarking: L43



1

3

2

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS FOR ONE DIODE

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	30	V
Forward Continuous Current at T _{amb} = 25 °C	IF	2001)	mA
Repetitive Peak Forward Current at $T_{amb} = 25 \text{ °C}$	I _{FRM}	300 ¹⁾	mA
Surge Forward Current at t _p < 1 s, T _{amb} = 25 °C	I _{FSM}	600 ¹⁾	mA
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _S	-65 to +150	°C
¹⁾ Device on fiberglass substrate, see layout.	· · ·		

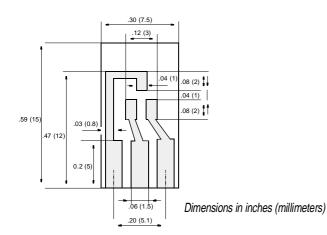


BAT54 THRU BAT54S

ELECTRICAL CHARACTERISTICS

Ratings for one diode at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage tested with 100 μA Pulses	V _{(BR)R}	30	-	-	V
Forward Voltage Pulse Test $t_p < 300 \ \mu s$, $\delta < 2\%$ at $I_F = 0.1 \ mA$ at $I_F = 1 \ mA$ at $I_F = 10 \ mA$ at $I_F = 30 \ mA$ at $I_F = 100 \ mA$	V _F V _F V _F V _F	- - - -	- - - -	240 320 400 500 1000	mV mV mV mV mV
Leakage Current Pulse Test t _p < 300 μs, δ < 2% at V _R = 25 V	I _R	-	-	2	μΑ
Capacitance at V _F = 1 V, f = 1 MHz	C _{tot}	-	-	10	pF
Reverse Recovery Time from I _F = 10 mA through I _R = 10 mA to I _R = 1 mA, R _L = 100 Ω	t _{rr}	-	-	5	ns
Thermal Resistance Junction to Ambient Air	R _{thJA}	-	_	430 ¹⁾	K/W
¹⁾ Device on fiberglass substrate, see layout					



Layout for R_{thJA} test Thickness: Fiberglass 0.059 in (1.5 mm) Copper leads 0.012 in (0.3 mm)

